

## High Speed Infrared Emitting Diode, 940 nm, GaAlAs Double Hetero



21531

### DESCRIPTION

VSMB1940X01 is an infrared, 940 nm emitting diode in GaAlAs Double Hetero technology with high radiant power and high speed, molded in clear, untinted 0805 plastic package for surface mounting (SMD).

### FEATURES

- Package type: surface mount
- Package form: 0805
- Dimensions (L x W x H in mm): 2 x 1.25 x 0.85
- AEC-Q101 qualified
- Peak wavelength:  $\lambda_p = 940$  nm
- High reliability
- High radiant power
- High radiant intensity
- High speed
- Angle of half sensitivity:  $\phi = \pm 60^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- 0805 standard surface-mountable package
- Floor life: 168 h, MSL 3, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
**GREEN**  
(5-2008)

### APPLICATIONS

- High speed IR data transmission
- High power emitter for low space applications
- High performance transmissive or reflective sensors

### PRODUCT SUMMARY

| COMPONENT   | $I_e$ (mW/sr) | $\phi$ (deg) | $\lambda_p$ (nm) | $t_r$ (ns) |
|-------------|---------------|--------------|------------------|------------|
| VSMB1940X01 | 6             | $\pm 60$     | 940              | 15         |

#### Note

- Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

| ORDERING CODE | PACKAGING     | REMARKS                      | PACKAGE FORM |
|---------------|---------------|------------------------------|--------------|
| VSMB1940X01   | Tape and reel | MOQ: 3000 pcs, 3000 pcs/reel | 0805         |

#### Note

- MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

| PARAMETER                           | TEST CONDITION                          | SYMBOL     | VALUE         | UNIT             |
|-------------------------------------|-----------------------------------------|------------|---------------|------------------|
| Reverse voltage                     |                                         | $V_R$      | 5             | V                |
| Forward current                     |                                         | $I_F$      | 100           | mA               |
| Peak forward current                | $t_p/T = 0.1$ , $t_p = 100 \mu\text{s}$ | $I_{FM}$   | 200           | mA               |
| Surge forward current               | $t_p = 100 \mu\text{s}$                 | $I_{FSM}$  | 1             | A                |
| Power dissipation                   |                                         | $P_V$      | 160           | mW               |
| Junction temperature                |                                         | $T_j$      | 100           | $^\circ\text{C}$ |
| Operating temperature range         |                                         | $T_{amb}$  | - 40 to + 85  | $^\circ\text{C}$ |
| Storage temperature range           |                                         | $T_{stg}$  | - 40 to + 100 | $^\circ\text{C}$ |
| Soldering temperature               | $t \leq 5$ s, 2 mm from case            | $T_{sd}$   | 260           | $^\circ\text{C}$ |
| Thermal resistance junction/ambient | J-STD-051, leads 7 mm, soldered on PCB  | $R_{thJA}$ | 270           | K/W              |

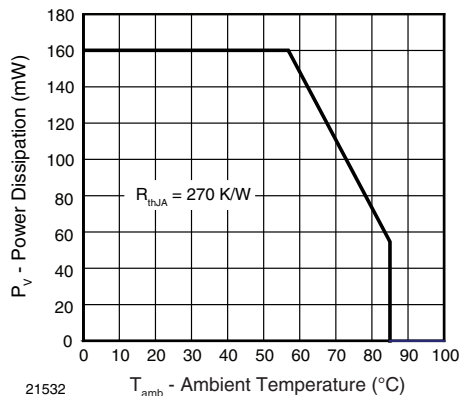


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

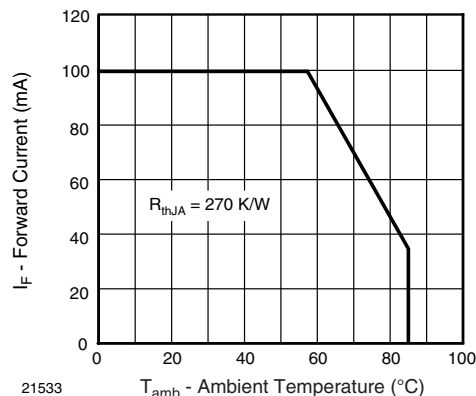


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS (T <sub>amb</sub> = 25 °C, unless otherwise specified) |                                                              |                             |      |        |      |       |
|------------------------------------------------------------------------------|--------------------------------------------------------------|-----------------------------|------|--------|------|-------|
| PARAMETER                                                                    | TEST CONDITION                                               | SYMBOL                      | MIN. | TYP.   | MAX. | UNIT  |
| Forward voltage                                                              | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms              | V <sub>F</sub>              | 1.15 | 1.35   | 1.6  | V     |
|                                                                              | I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs                | V <sub>F</sub>              |      | 2.2    |      | V     |
| Temperature coefficient of V <sub>F</sub>                                    | I <sub>F</sub> = 1 mA                                        | TK <sub>V<sub>F</sub></sub> |      | - 1.5  |      | mV/K  |
|                                                                              | I <sub>F</sub> = 100 mA                                      | TK <sub>V<sub>F</sub></sub> |      | - 1.1  |      | mV/K  |
| Reverse current                                                              | V <sub>R</sub> = 5 V                                         | I <sub>R</sub>              |      |        | 10   | μA    |
| Junction capacitance                                                         | V <sub>R</sub> = 0 V, f = 1 MHz,<br>E = 0 mW/cm <sup>2</sup> | C <sub>J</sub>              |      | 70     |      | pF    |
| Radiant intensity                                                            | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms              | I <sub>e</sub>              | 3    | 6      | 12   | mW/sr |
|                                                                              | I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs                | I <sub>e</sub>              |      | 60     |      | mW/sr |
| Radiant power                                                                | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms              | φ <sub>e</sub>              |      | 40     |      | mW    |
| Temperature coefficient of radiant power                                     | I <sub>F</sub> = 1 mA                                        | TK <sub>φ<sub>e</sub></sub> |      | - 1.1  |      | %/K   |
|                                                                              | I <sub>F</sub> = 100 mA                                      | TK <sub>φ<sub>e</sub></sub> |      | - 0.51 |      | %/K   |
| Angle of half intensity                                                      |                                                              | φ                           |      | ± 60   |      | deg   |
| Peak wavelength                                                              | I <sub>F</sub> = 30 mA                                       | λ <sub>p</sub>              |      | 940    |      | nm    |
| Spectral bandwidth                                                           | I <sub>F</sub> = 30 mA                                       | Δλ                          |      | 25     |      | nm    |
| Temperature coefficient of λ <sub>p</sub>                                    | I <sub>F</sub> = 30 mA                                       | TK <sub>λ<sub>p</sub></sub> |      | 0.25   |      | nm    |
| Rise time                                                                    | I <sub>F</sub> = 100 mA, 20 % to 80 %                        | t <sub>r</sub>              |      | 15     |      | ns    |
| Fall time                                                                    | I <sub>F</sub> = 100 mA, 20 % to 80 %                        | t <sub>f</sub>              |      | 15     |      | ns    |
| Virtual source diameter                                                      |                                                              | d                           |      | 0.5    |      | mm    |

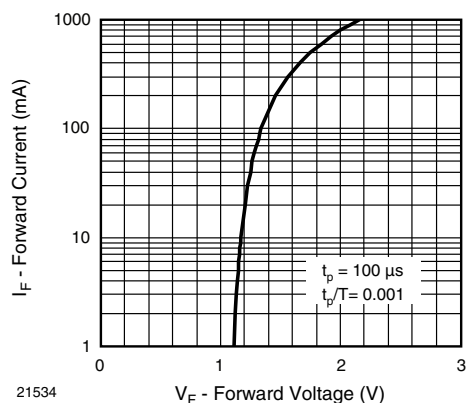
**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)


Fig. 3 - Forward Current vs. Forward Voltage

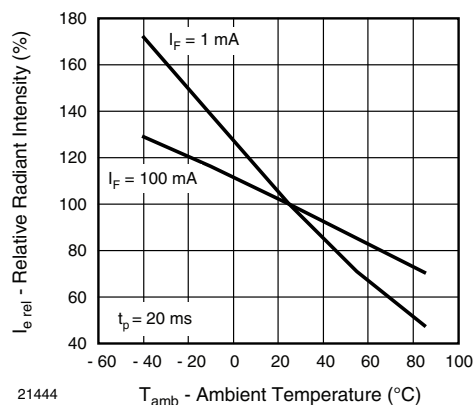


Fig. 6 - Relative Radiant Intensity vs. Ambient Temperature

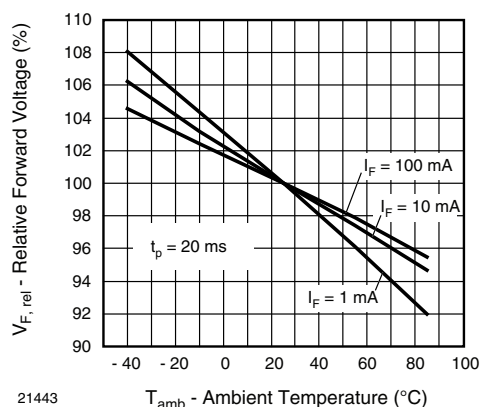


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

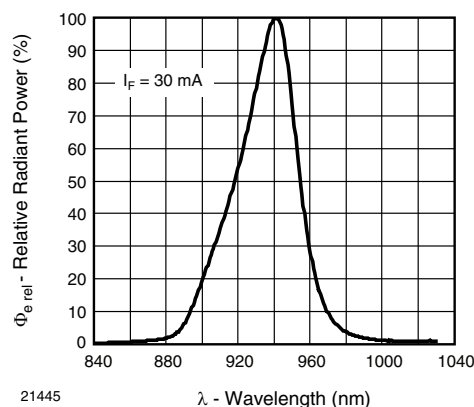


Fig. 7 - Relative Radiant Power vs. Wavelength

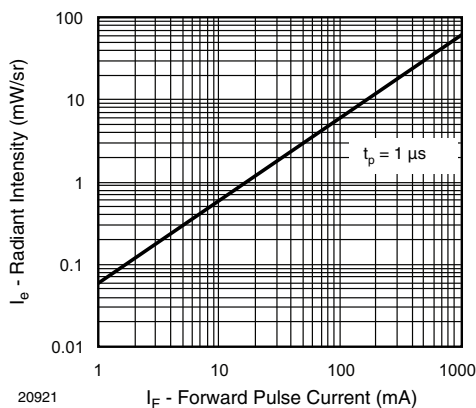


Fig. 5 - Radiant Intensity vs. Forward Current

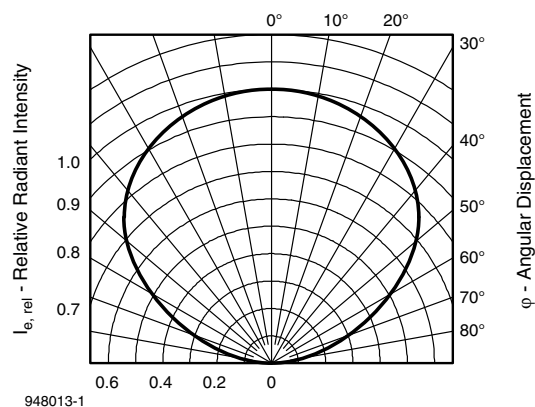


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

## REFLOW SOLDER PROFILE

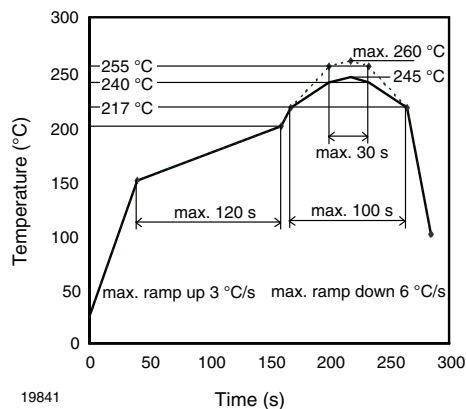


Fig. 9 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

## DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

## FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:

Moisture sensitivity: level 3

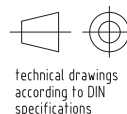
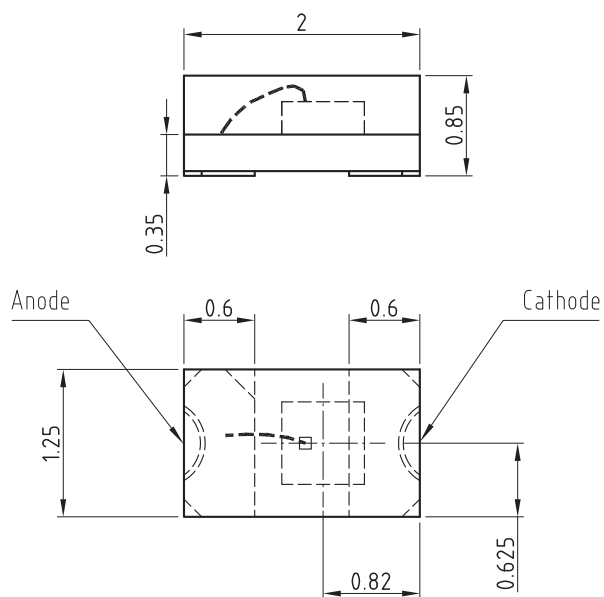
Floor life: 168 h

Conditions:  $T_{amb} < 30^{\circ}\text{C}$ , RH < 60 %

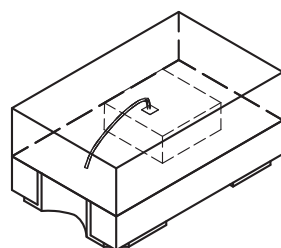
## DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at  $40^{\circ}\text{C}$  (+  $5^{\circ}\text{C}$ ), RH < 5 %.

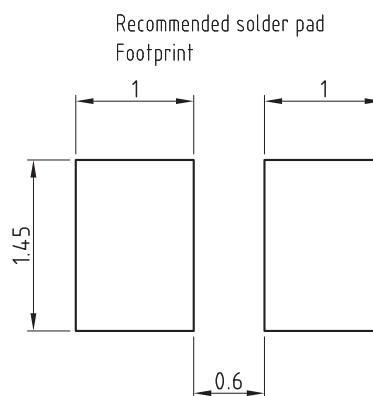
## PACKAGE DIMENSIONS in millimeters

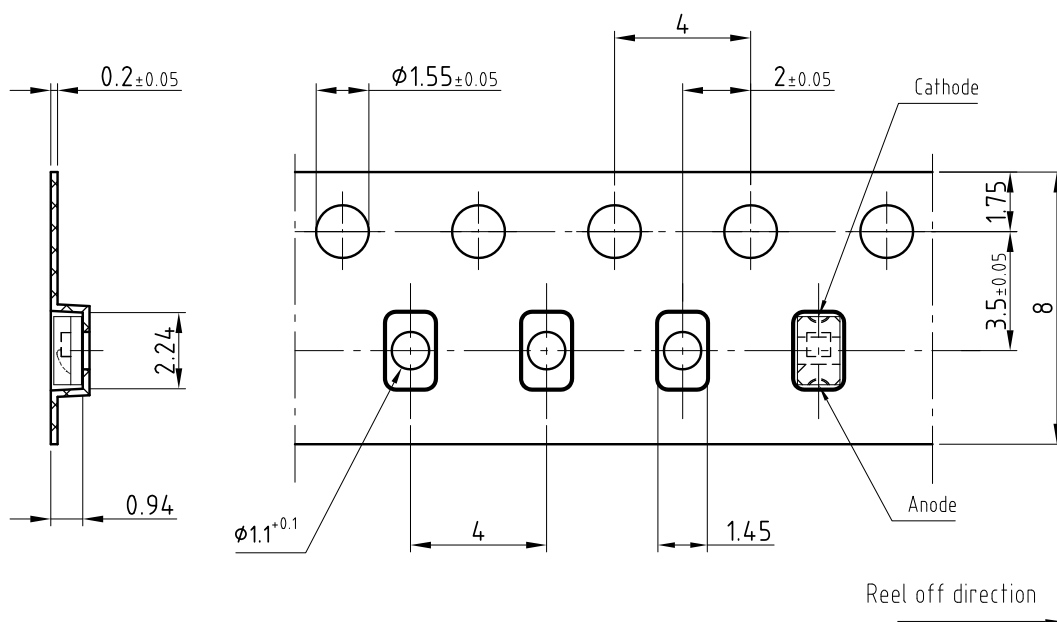


Not indicated tolerances  $\pm 0.1$



Drawing-No.: 6.541-5064.01-4  
Issue: 2; 23.02.07  
20018



**BLISTER TAPE DIMENSIONS** in millimeters

technical drawings  
according to DIN  
specifications

Drawing-No.: 9.700-5311.01-4

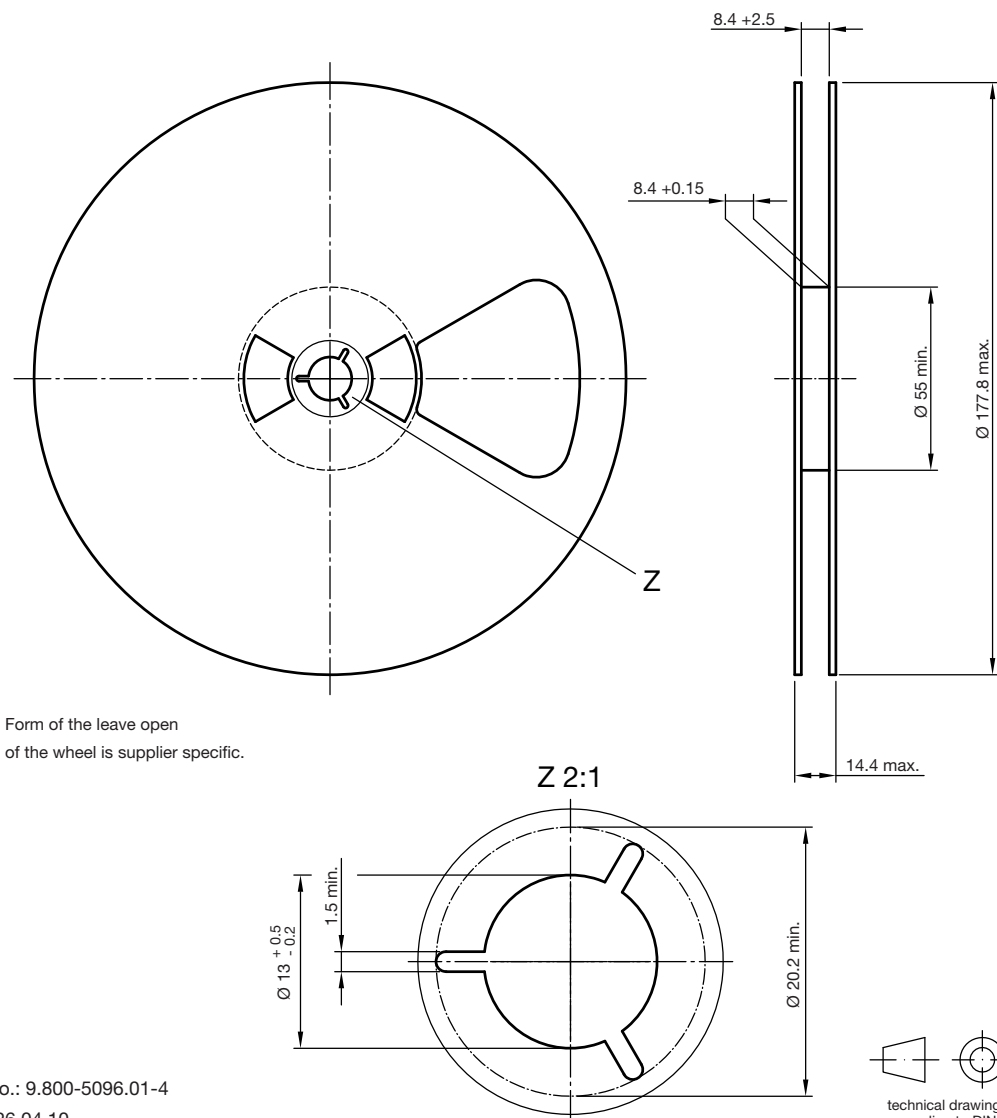
Issue: 1; 23.02.07

21501

Not indicated tolerances  $\pm 0.1$



**REEL DIMENSIONS** in millimeters



Drawing-No.: 9.800-5096.01-4

Issue: 2; 26.04.10

20875



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